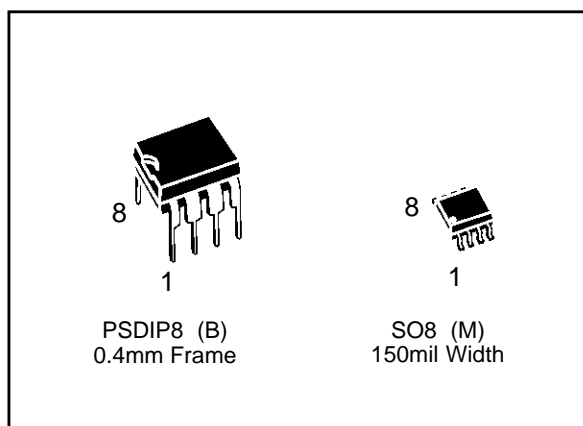


SERIAL MICROWIRE BUS 2K (128 x 16 or 256 x 8) EEPROM

DATA BRIEFING

- 1 MILLION ERASE/WRITE CYCLES, with 40 YEARS DATA RETENTION
- DUAL ORGANIZATION: 128 x 16 or 256 x 8
- BYTE/WORD and ENTIRE MEMORY PROGRAMMING INSTRUCTIONS
- SELF-TIMED PROGRAMMING CYCLE with AUTO-ERASE
- READY/BUSY SIGNAL DURING PROGRAMMING
- SINGLE SUPPLY VOLTAGE:
 - 4.5V to 5.5V for ST93C56 version
 - 3V to 5.5V for ST93C57 version
- SEQUENTIAL READ OPERATION
- 5ms TYPICAL PROGRAMMING TIME

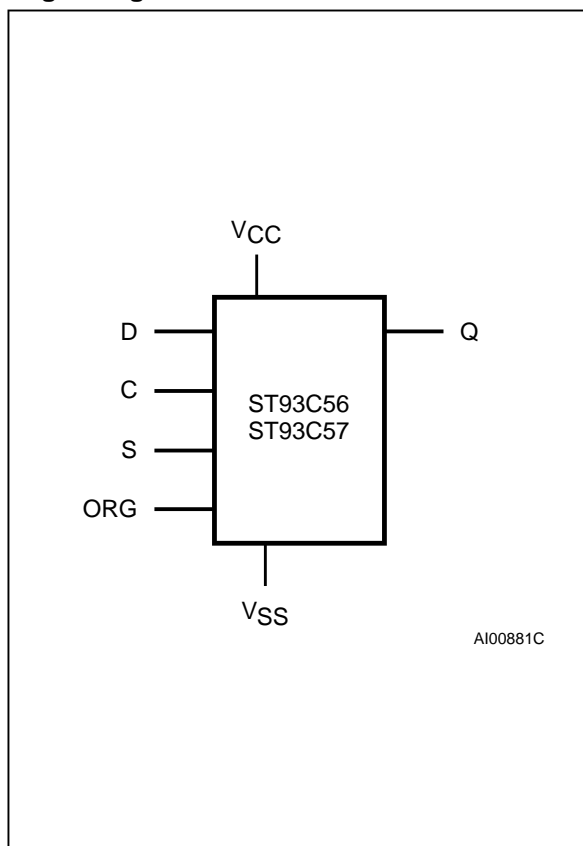


DESCRIPTION

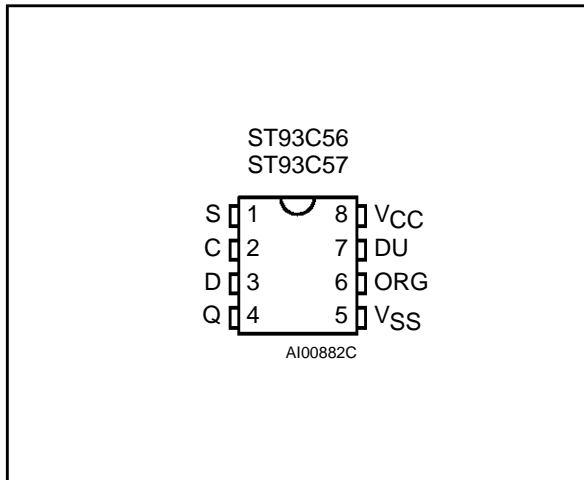
This specification covers a range of 2K bit serial EEPROM products, the ST93C56, 56C specified at $5V \pm 10\%$ and the ST93C57C specified at 3V to 5.5V. In the text, products are referred to as ST93C56.

The ST93C56 is a 2K bit Electrically Erasable Programmable Memory (EEPROM) fabricated with SGS-THOMSON's High Endurance Single Polysilicon CMOS technology. The memory is accessed through a serial input (D) and output (Q). The 2K bit memory is divided into either 256 x 8 bit bytes or 128 x 16 bit words. The organization may be selected by a signal applied on the ORG input.

Logic Diagram

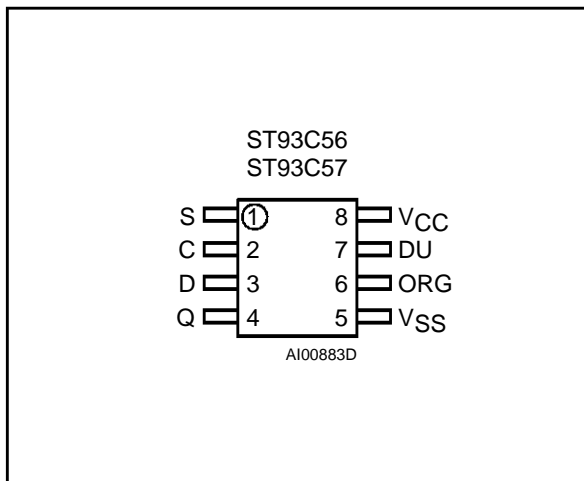


DIP Pin Connections



Warning: DU = Don't Use

SO Pin Connections



Warning: DU = Don't Use

Signal Names

S	Chip Select Input
D	Serial Data Input
Q	Serial Data Output
C	Serial Clock
ORG	Organisation Select
V _{CC}	Supply Voltage
V _{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: ST93C56C M 1 013TR

Operating Voltage	
56	4.5V to 5.5V
57	3V to 5.5V
Revision	
blank	CMOS F3
C	CMOS F4
Package	
B	PSDIP8 0.4mm Frame
M	SO8 150mil Width
Temp. Range	
1	0 to 70 °C
6	-40 to 85 °C
3	-40 to 125 °C
Option	
013TR	Tape & Reel Packing (A, T ver.)
TR	Tape & Reel Packing (C version)